Elektronische Bauelemente

2SA1576F

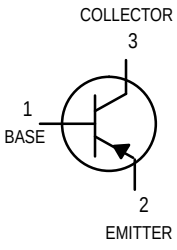
PNP Silicon

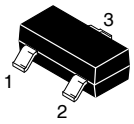
General Purpose Transistor

RoHS Compliant Product

Feature

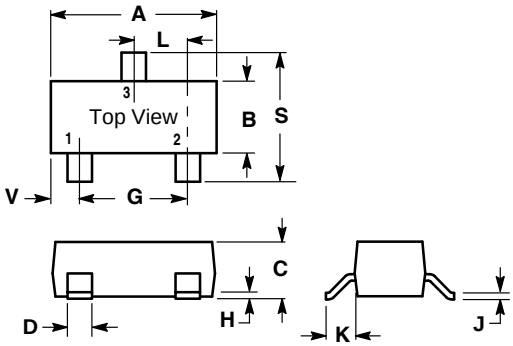
- Complements the 2SC4081F





Marking Code: 5AX

X = hFE Rank Code



SOT-323		
Dim	**Min**	**Max**
A	1.800	2.200
B	1.150	1.350
C	0.800	1.000
D	0.300	0.400
G	1.200	1.400
H	0.000	0.100
J	0.100	0.250
K	0.350	0.500
L	0.590	0.720
S	2.000	2.400
V	0.280	0.420
All Dimension in mm		

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	VCBO	-60	V
Collector to Emitter Voltage	VCEO	-50	V
Emitter to Base Voltage	VEBO	-6	V
Collector Current	IC	-150	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25℃

Parameter	Symbol	Min	Typ.	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-60	-	-	V	I_C=-50uA
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50	-	-	V	I_C=-1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-6	-	-	V	I_E=-50uA
Collector-Emitter Breakdown Voltage	I_{CBO}	-	-	-100	nA	V_{CB}=-60V
Emitter-Base Cutoff Current	I_{EBO}	-	-	-100	nA	V_{EB}=-6V
Collector Saturation Voltage 1	$V_{CE(sat)}$	-	-	-500	mV	I_C=-50mA, I_B=-5mA
DC Current Gain	h_{FE}	120	-	560	-	V_{CE}=-6V, I_C=-1mA
Gain-Bandwidth Product	fT	-	140	-	MHz	V_{CE}=-12V, I_E=-2mA, f=100MHz
Output Capacitance	Cob	-	4.0	5.0	pF	V_{CB}=-12V, f=1MHz, I_E=0

*Pulse Test: Pulse Width = 380us, Duty Cycle = 2%

Classification of hFE

Rank	Q	R	S
Range	**120 - 270**	**180 - 390**	**270 - 560**

Characteristics Curve

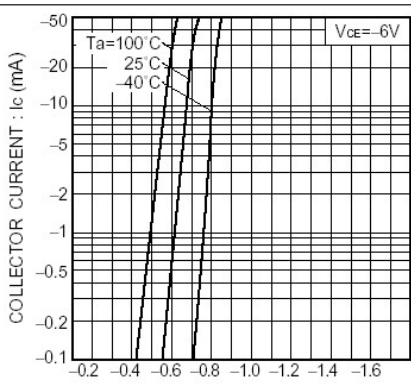


Fig.1 Grounded emitter propagation characteristics

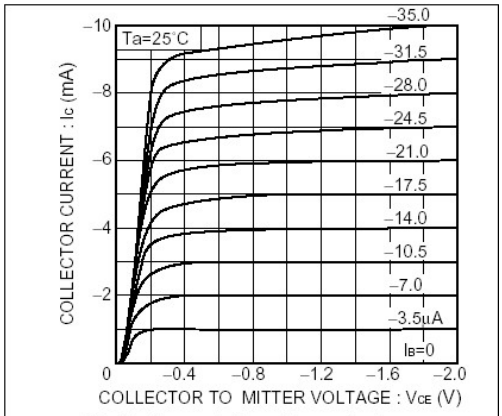


Fig.2 Grounded emitter output characteristics (I)

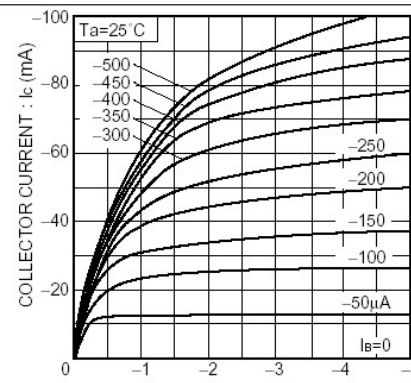


Fig.3 Grounded emitter output characteristics (II)

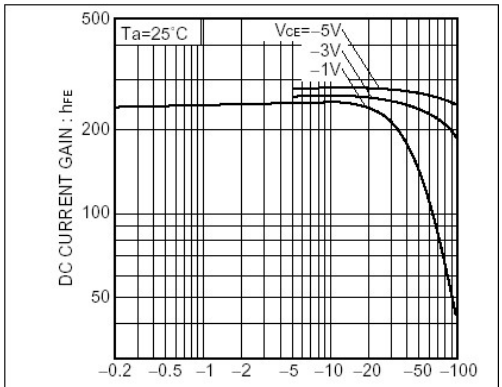


Fig.4 DC current gain vs. collector current (I)

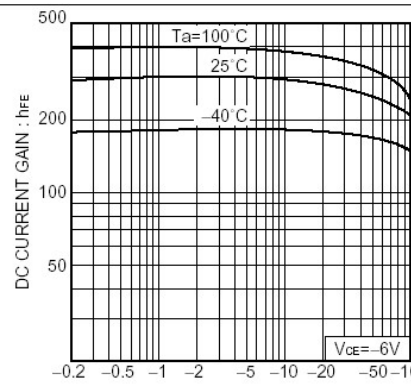


Fig.5 DC current gain vs. collector current (II)

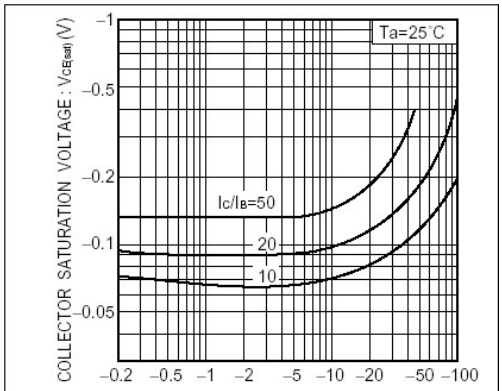


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

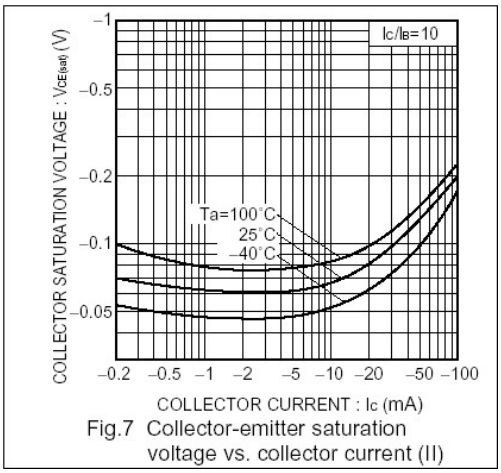


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

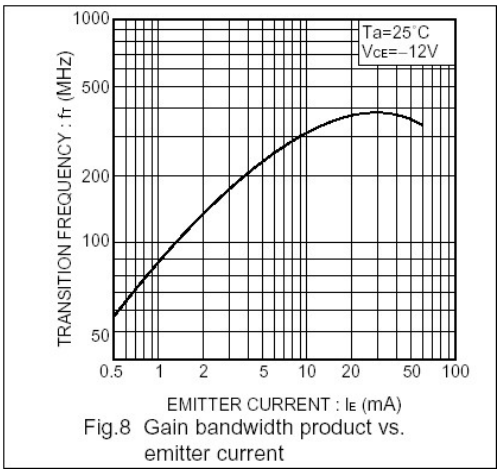


Fig.8 Gain bandwidth product vs. emitter current

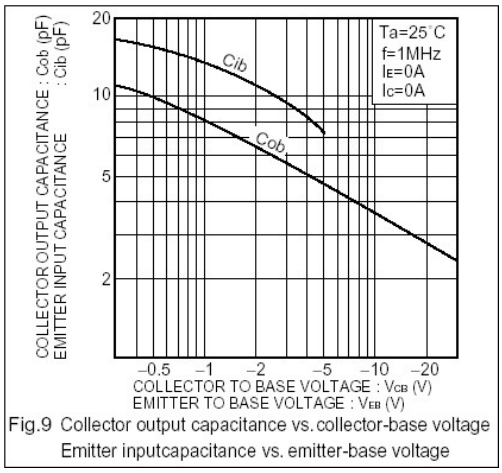


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter inputcapacitance vs. emitter-base voltage